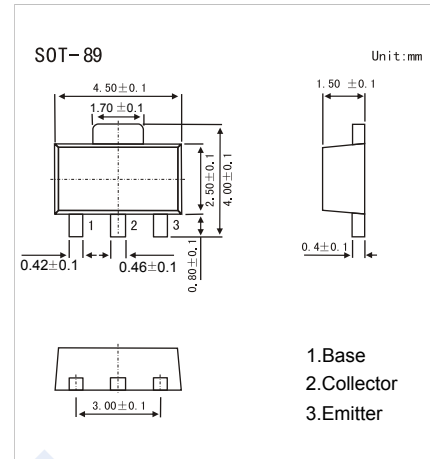


PNP Transistors

2SA1463

■ Features

- High speed ,high voltage switching
- Low collector saturaton voltage
- Complementary to 2SC3736



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-60	V
Collector - Emitter Voltage	V _{CEO}	-45	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _c	-1	A
Collector Current - Pulse *	I _{CP}	-2	
Collector Power Dissipation	P _c	2	W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

* : Pulsed:PW ≤ 10ms,Duty Cycle ≤ 50%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 μA, I _E = 0	-60			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = -1 mA, I _B = 0	-45			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _c = 0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -60 V, I _E = 0			-0.5	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -4V, I _c = 0			-0.5	
Collector-emitter saturation voltage *	V _{CE(sat)}	I _c = -500 mA, I _B = -50 mA		-0.26	-0.6	V
Base - emitter saturation voltage *	V _{BE(sat)}	I _c = -500 mA, I _B = -50 mA		-0.98	-1.2	
DC current gain *	h _{FE(1)}	V _{CE} = -10V, I _c = -50mA	60		200	
	h _{FE(2)}	V _{CE} = -10V, I _c = -500mA	60			
Turn-on time	t _{on}	I _c = -500mA, I _{B1} = -I _{B2} = -50mA		25	40	ns
Storage time	t _{stg}			46	70	
Turn -off time	t _{off}			62	100	
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		11	25	pF
Transition frequency	f _T	V _{CE} = -10V, I _E = 100mA	300	400		MHz

* : Pulsed:PW ≤ 350us,Duty Cycle ≤ 2%

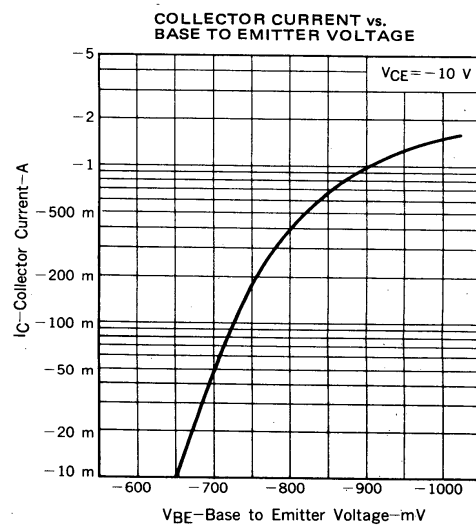
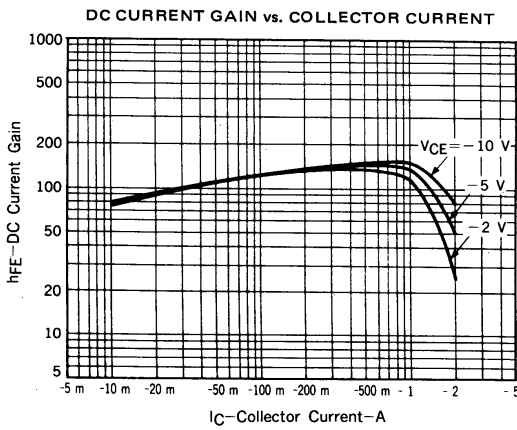
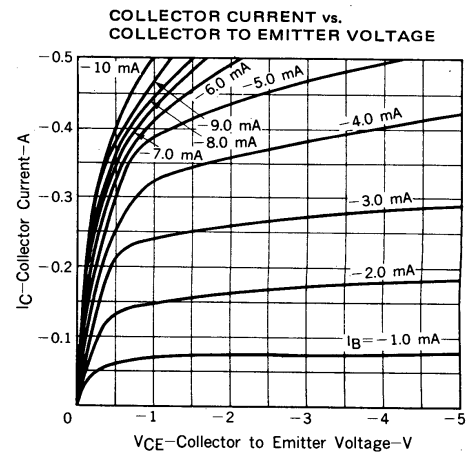
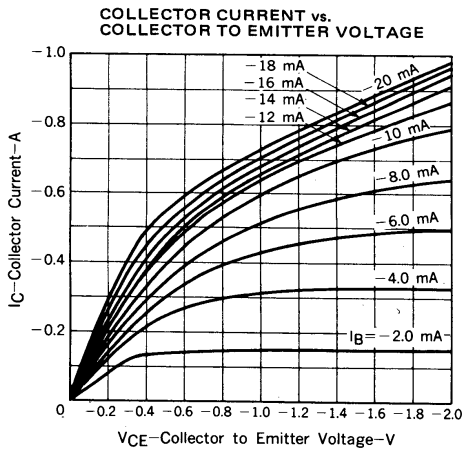
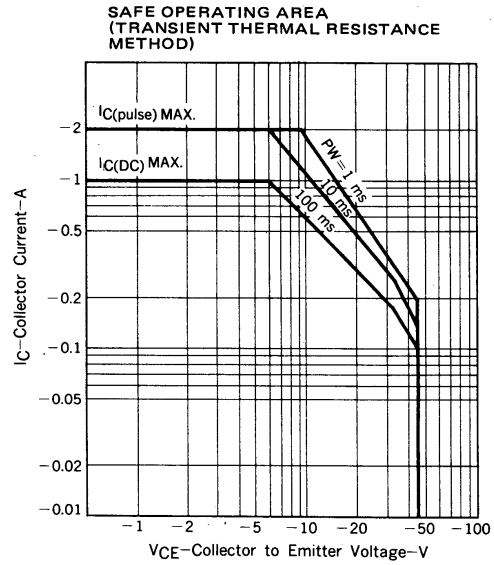
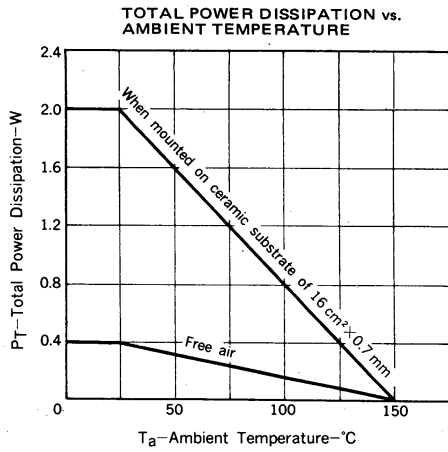
■ Classification of h_{FE(1)}

Type	2SA1463-L	2SA1463-K
Range	60-120	100-200
Marking	IL	IK

PNP Transistors

2SA1463

■ Typical Characteristics



PNP Transistors

2SA1463

■ Typical Characteristics

